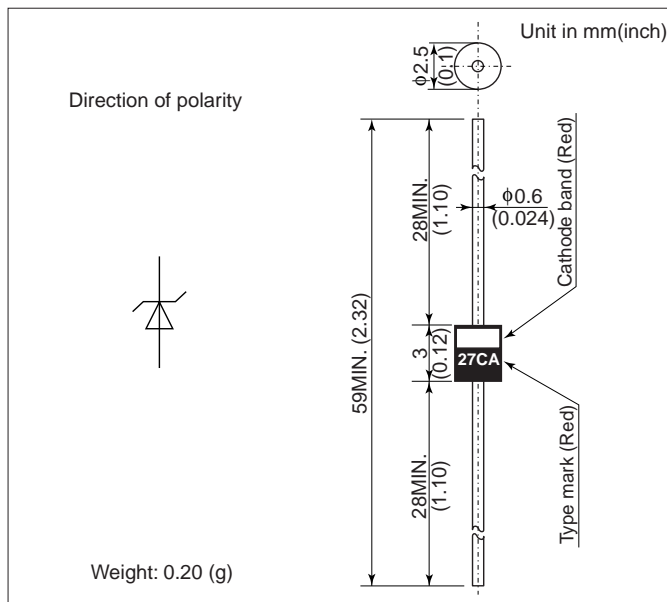


DAM1SA

FEATURES

- High transient reverse power capability suitable for protecting automobile electronic components etc.
- Diffused-junction. Resin encapsulated.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

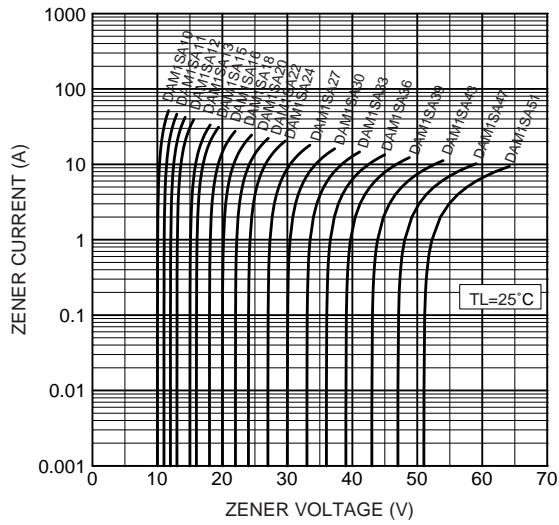
Items	Symbols	Units	Ratings
Non-Repetitive Peak Reverse One-Cycle Dissipation	P_{RSM}	W	600(Rectangular pulse $t=0.1ms$ $T_i=25^\circ C$ start)
Operating Junction Temperature	T_j	$^\circ C$	-40 ~ +150
Storage Temperature	T_{stg}	$^\circ C$	-40 ~ +150
DC Reverse Voltage	V_{DC}	V	Refer to characteristics column

CHARACTERISTICS($T_L=25^\circ C$)

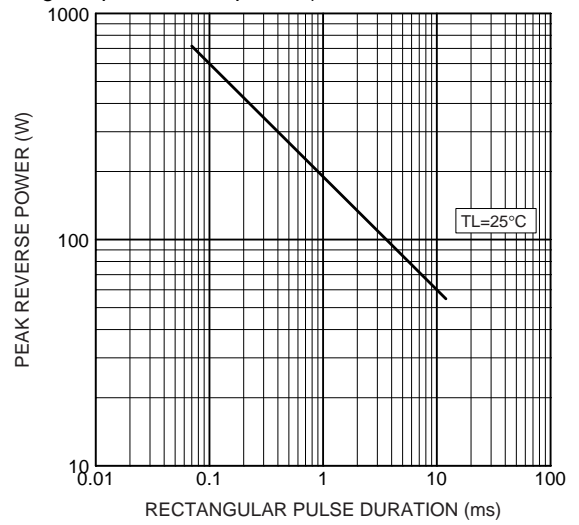
Type	DC Reverse Voltage V_{DC} (V)	Characteristics				Maximum Reverse Current	
		Zener Voltage V_z (V)		Maximum Dynamic Impedance Z_z (ohm)	Test Current I_z (mA)	I_{RRM} (μA)	V_R (V)
		Minimum	Maximum				
DAM1SA10	7	9.4	10.6	15	25	50	7
DAM1SA11	8	10.4	11.6	15	25	50	8
DAM1SA12	9	11.4	12.7	15	25	50	9
DAM1SA13	10	12.4	14.1	15	25	50	10
DAM1SA15	11	13.5	15.6	15	25	50	11
DAM1SA16	12	15.3	17.1	15	15	50	12
DAM1SA18	13	16.8	19.1	15	15	50	13
DAM1SA20	14	18.8	21.2	15	15	50	14
DAM1SA22	16	20.8	23.3	15	15	50	16
DAM1SA24	18	22.7	25.6	15	10	50	18
DAM1SA27	20	25.1	28.9	15	10	50	20
DAM1SA30	22	28.0	32.0	15	10	50	22
DAM1SA33	24	31.0	35.0	15	10	50	24
DAM1SA36	26	33.4	38.6	15	10	50	26
DAM1SA39	28	36.1	41.9	30	10	50	28
DAM1SA43	31	39.8	46.2	30	6	50	31
DAM1SA47	34	43.3	50.7	30	6	50	34
DAM1SA51	37	46.9	55.1	30	6	50	37

DAM1SA

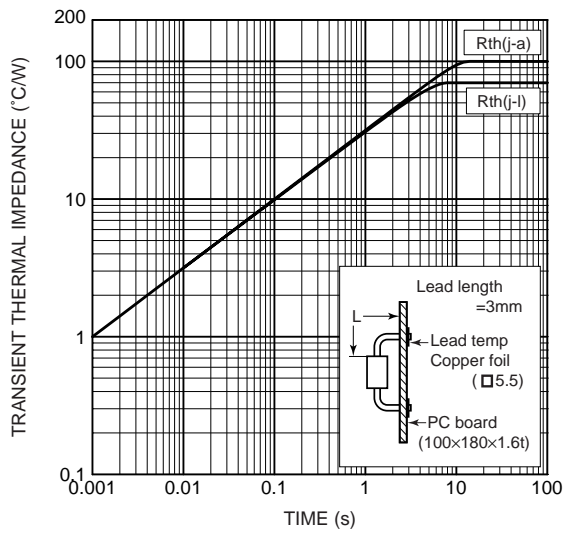
Typical zener characteristics



Typical reverse power characteristic (Rectangular pulse non-repetitive)



Transient thermal impedance



HITACHI POWER SEMICONDUCTORS

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